650V 20A SiC Schottky Diode – SiS650S20AS

Silicon Carbide Schottky Barrier Rectifier diode in bare die form

Capable of high temperature operation >= 175°C

No Reverse Recovery / No Forward Recovery

No suffix - MIL-STD-750 /2073 Visual Inspection

+ MIL-PRF-38534 Class H LAT

+ MIL-PRF-38534 Class K LAT

"H" - MIL-STD-750 /2073 Visual Inspection

"K" - MIL-STD-750 /2073 Visual Inspection

For further information on LAT process flows see below.

www.siliconsupplies.com/quality/bare-die-lot-qualification

Default – Die in Waffle Pack (100 per tray capacity)

With additional electrical selection - By specific request

Sawn Wafer on Tape - By specific request

Unsawn Wafer - By specific request

High Frequency Operation

Ordering Information:

The following part suffixes apply:

LAT = Lot Acceptance Test.

Supply Formats:

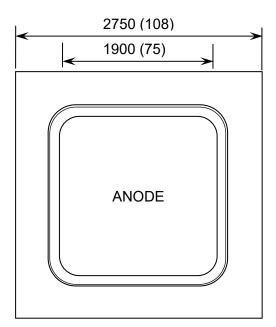
High Surge Current Capability

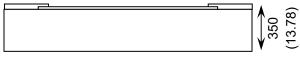
Positive Temperature Coefficient

Die Dimensions in µm (mils)

Rev 1.0

30/10/23





CHIP BACKSIDE IS CATHODE

Mechanical Specification

Die Size (Unsawn)	2750 x 2750 108 x 108	µm mils	
Anode Pad Size	1900 x 1900 75 x 75	µm mils	
Die Thickness	350 (±20) 13.78 (0.79)	µm mils	
Top Metal Composition	Al 4µm		
Back Metal Composition	Ag 0.4µm		

Features:





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Absolute Maximum Ratings T_J = 25°C unless otherwise stated

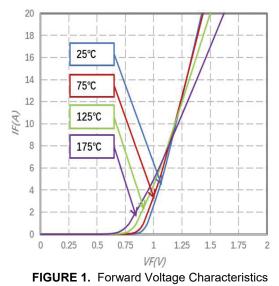
PARAMETER	SYMBOL	VALUE	UNIT	
Repetitive peak reverse voltage	V _{RRM}	650	V	
Surge peak reverse voltage	V _{RSM}	650	V	
DC Peak Blocking Voltage	V _{BR}	650	V	
Average forward rectified current	I _{F(AV)}	20	A	
Repetitive Peak Forward Surge Current	I _{FRM}	105	A	
Peak Single-Cycle Non-Repetitive Surge Current	I _{FSM}	170	А	
Operating Junction temperature	TJ	-55 to 175	°C	
Storage Temperature Range	T _{STG}	-65 to 175	°C	

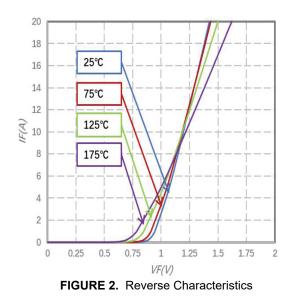
Electrical Characteristics T_J = 25°C unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	ΤΥΡ	MAX	UNIT
Maximum instantaneous forward voltage ¹	V _{F1}	V _{RRM} = 650V, I _{FM} = 20A	-	1.45	1.70	V
	V _{F2}	V_{RRM} = 650V, I_{FM} = 20A, T_{J} = 175°C	-	1.65	2.00	v
Maximum reverse leakage current ¹	I _{RM} @ V _{RM}	V _R = 650V	-	1.5	50	μΑ
		V _R = 650V, T _J = 175°C	-	15	200	
Junction Capacitance	CT	V _R = 0V, f = 1MHz,	-	1550	-	pF
Reverse Recovery Charge	Q _C	V_R = 400V , I_F = 20A, di/dt = 200A/µs	-	96.7	-	nC
Capacitance Stored Energy	Ec	V _R = 400V	-	23.69	-	μJ

1. Pulse Width \leq 300µs, Duty Cycle \leq 2.0%

Typical Characteristics T_J = 25°C









Typical Characteristics T_J = 25°C unless otherwise stated

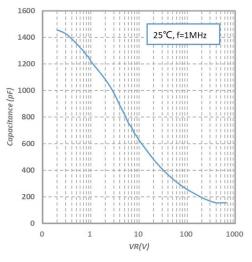


FIGURE 3. Capacitance Versus Reverse Voltage

60

50

40

(T) 30

20

10

0

n

100

200

300

VR(V)

FIGURE 5. Capacitance Stored Energy

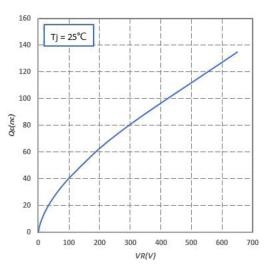
400

500

600

700

Tj = 25°C



30/10/23

FIGURE 4. Total Capacitance Charge Versus Reverse Voltage

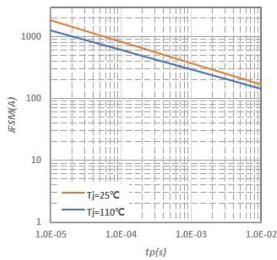


FIGURE 6. Non-repetitive Peak Forward Surge Current Versus Pulse Duration

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